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Q6s	USPAT:US PGPUB; EPO; JPO; DERWENT; IDM; TDB		
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<div>(((second-another upper, top) adj ((ferroelectric ferro adj electric)) near (ayer film))) near9 (temperature (trug\$4 rough\$4 asperit\$4)))) 09/842631</div> <div>oct 2004</div>			

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U-1	Inventor	Document	Issue	P	Title	Current	Current XN	Re/View	S	C	P	4	5	6	7	8	9	10	11	12	Image	Doc.	P
1	Li, Tingkai et al	US 6864116	2003/1	7	Seed layer processes for MOCVD of ferroele	438/3			F	F	F	F	F	F	F	F	F	F	F	F	US 6864116	F	
2	Zhen, Wendo	US 2001004	2001/1	2	Semiconductor device having ferroelectric t	438/3	257/E21.01		F	F	F	F	F	F	F	F	F	F	F	F	US 2001004	F	
3	ZHEN, W	EP 1150344	2003/0	2	Manufacture of semiconductor device having				F	F	F	F	F	F	F	F	F	F	F	F	US 2001004	F	
4	Matsuura, Os	US 2004013	2004/0	1	Ferroelectric capacitor, process for producti	257/295			F	F	F	F	F	F	F	F	F	F	F	F	US 2004013	F	
5	Li, Tingkai et al	US 2003020	2003/1	8	Method of forming ferroelectric thin films on	438/3	438/763		F	F	F	F	F	F	F	F	F	F	F	F	US 2003020	F	
6	Li, Tingkai et al	US 2003010	2003/0	8	Seed layer processes for MOCVD of ferroele	438/3			F	F	F	F	F	F	F	F	F	F	F	F	US 2003010	F	
7	Jung, Dong-Ji	US 2002002	2002/0	1	Semiconductor device including ferroelectric	257/285	257/E21.02		F	F	F	F	F	F	F	F	F	F	F	F	US 2002002	F	
8	Shimada, Yas	US 2002002	2002/0	1	Semiconductor device and method for fabric	257/295	257/300		F	F	F	F	F	F	F	F	F	F	F	F	US 2002002	F	
9	Wikborg, Erla	US 2001005	2001/1	1	Electrically tunable device and a method rela	257/595	257/602		F	F	F	F	F	F	F	F	F	F	F	F	US 2001005	F	
10	Kawakubo, T	US 6787957	2004/0	1	Infrared detection element and infrared deta	250/338			F	F	F	F	F	F	F	F	F	F	F	F	US 6787957	F	